

ABSTRACT OF THE DISCLOSURE

The method for fabricating a semiconductor device comprises the steps of: forming a dummy electrode 22n and a dummy electrode 22p; forming a metal film 32 on the dummy electrode 22p; conducting a thermal treatment at a first temperature to substitute the dummy electrode 22n with an electrode 34a of a material containing the constituent material of the metal film 32; forming a metal film 36 on the dummy electrode 22n; and conducting a thermal treatment at a second temperature, which is lower than the first temperature and at which an interdiffusion of constituent materials between the electrode 34a and the metal film 36 does not take place, to substitute the second dummy electrode with an electrode 34b of a material containing the constituent material of the metal film 36.